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| SANYO | No.3704A | 2SC4635 |
| | | NPN Triple Diffused Planar Silicon Transistor High-Voltage Amp, High-Voltage Switching Applications |

Features

- High breakdown voltage ($V_{CEO \text{ min}} = 1500\text{V}$).
- Small Cob (typical Cob = 1.9pF).
- Full-isolation package.
- High reliability (Adoption of HVP process).

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

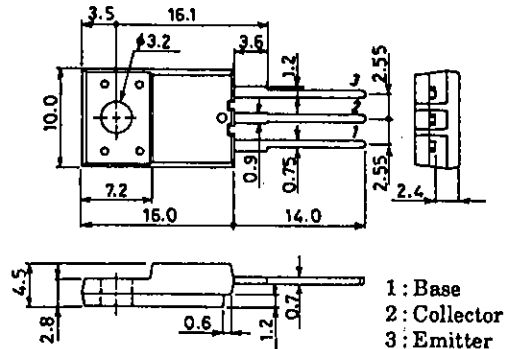
| | | | unit |
|------------------------------|-----------|-------------|------------------|
| Collector-to-Base Voltage | V_{CBO} | 1500 | V |
| Collector-to-Emitter Voltage | V_{CEO} | 1500 | V |
| Emitter-to-Base Voltage | V_{EBO} | 5 | V |
| Collector Current | I_C | 20 | mA |
| Collector Current (Pulse) | I_{CP} | 60 | mA |
| Collector Dissipation | P_C | 2 | W |
| Junction Temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage Temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |

Electrical Characteristics at $T_a = 25^\circ\text{C}$

| | | | min | typ | max | unit |
|--------------------------|---------------|---|------|-----|-----|--------------------|
| Collector Cutoff Current | I_{CBO} | $V_{CB} = 1500\text{V}, I_E = 0$ | | | 1 | μA |
| Emitter Cutoff Current | I_{EBO} | $V_{EB} = 4\text{V}, I_C = 0$ | | | 1 | μA |
| DC Current Gain | h_{FE} | $V_{CE} = 5\text{V}, I_C = 600\mu\text{A}$ | 10 | | 60 | |
| Gain-Bandwidth Product | f_T | $V_{CE} = 10\text{V}, I_C = 600\mu\text{A}$ | | 6 | | MHz |
| C-E Saturation Voltage | $V_{CE(sat)}$ | $I_C = 1.5\text{mA}, I_B = 0.3\text{mA}$ | | | 5 | V |
| B-E Saturation Voltage | $V_{BE(sat)}$ | $I_C = 1.5\text{mA}, I_B = 0.3\text{mA}$ | | | 2 | V |
| C-B Breakdown Voltage | $V_{(BR)CBO}$ | $I_C = 100\mu\text{A}, I_E = 0$ | 1500 | | | V |
| C-E Breakdown Voltage | $V_{(BR)CEO}$ | $I_C = 1\text{mA}, R_{BE} = \infty$ | 1500 | | | V |
| E-B Breakdown Voltage | $V_{(BR)EBO}$ | $I_E = 100\mu\text{A}, I_C = 0$ | 5 | | | V |
| Output Capacitance | Cob | $V_{CB} = 100\text{V}, f = 1\text{MHz}$ | | 1.9 | | pF |
| Thermal Resistance | R_{thj-c} | Junction - case | | | 8.3 | $^\circ\text{C/W}$ |

Package Dimensions 2079B

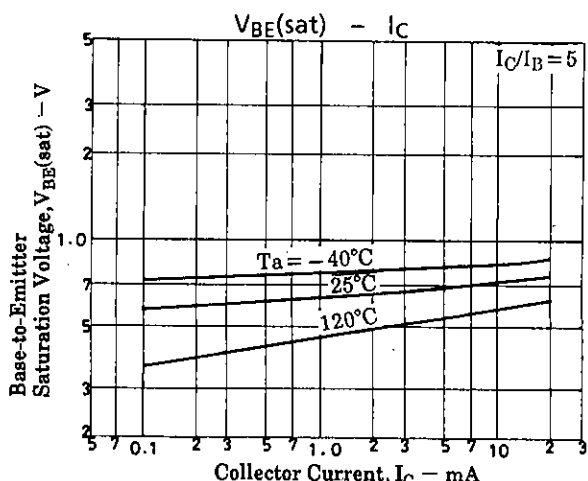
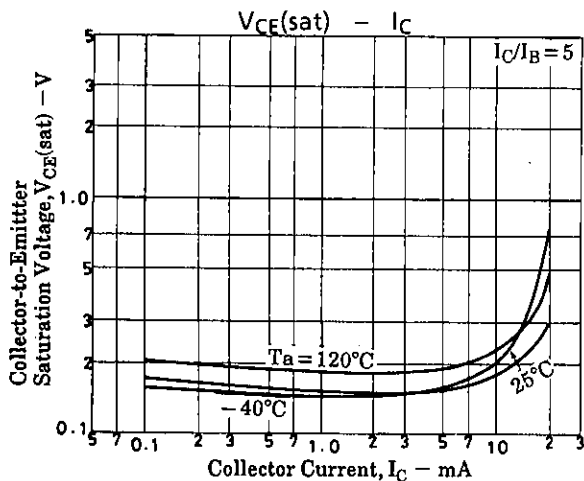
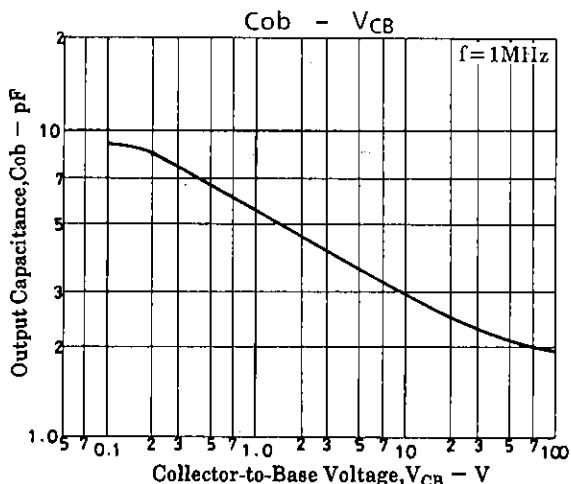
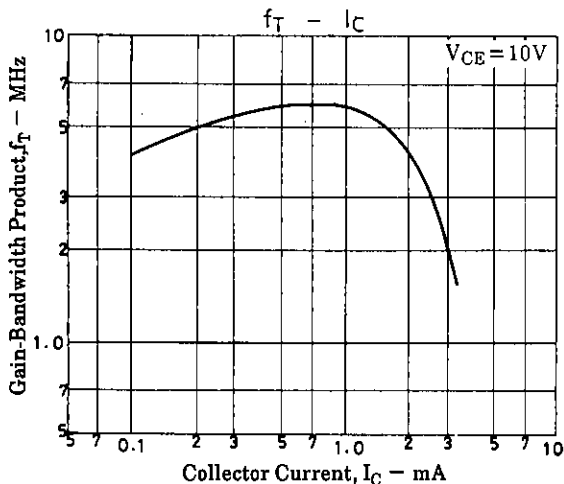
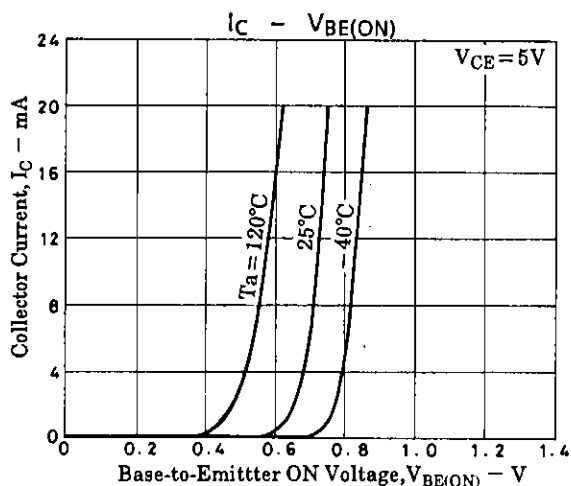
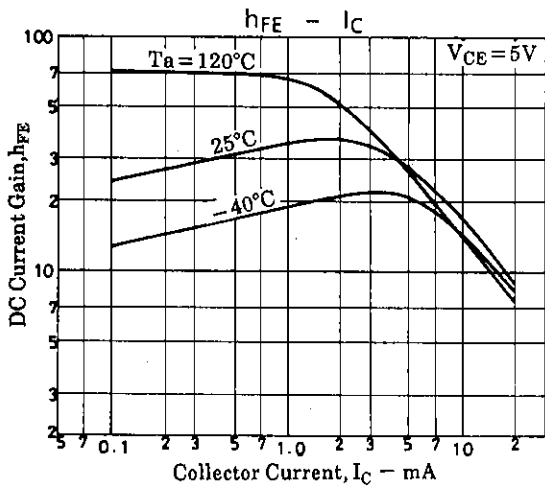
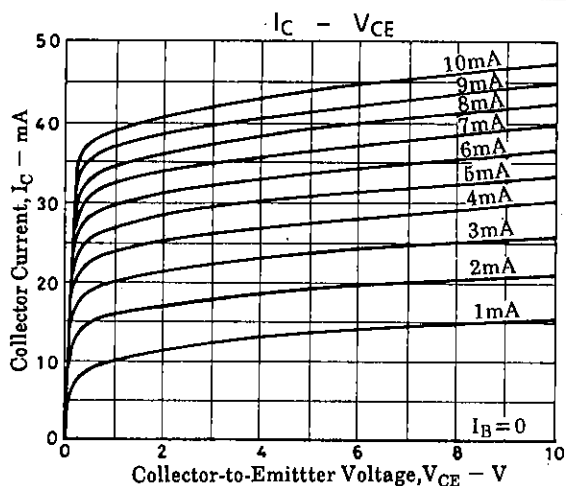
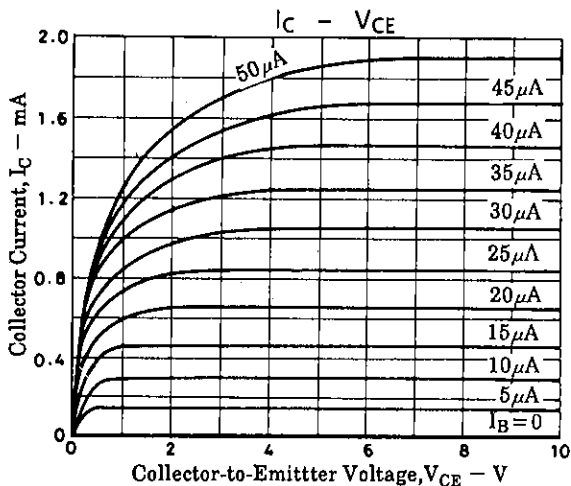
(unit : mm)

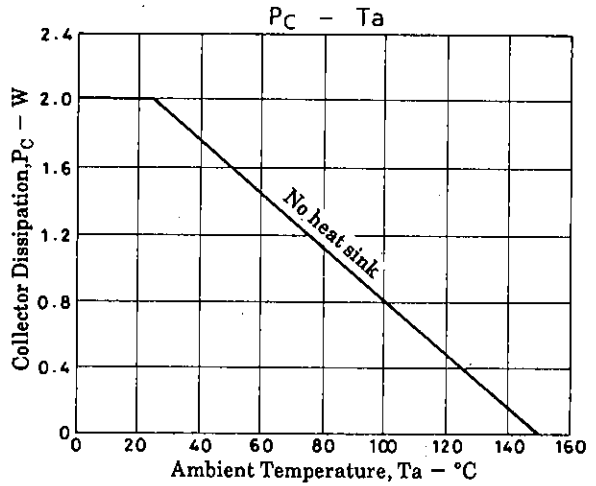
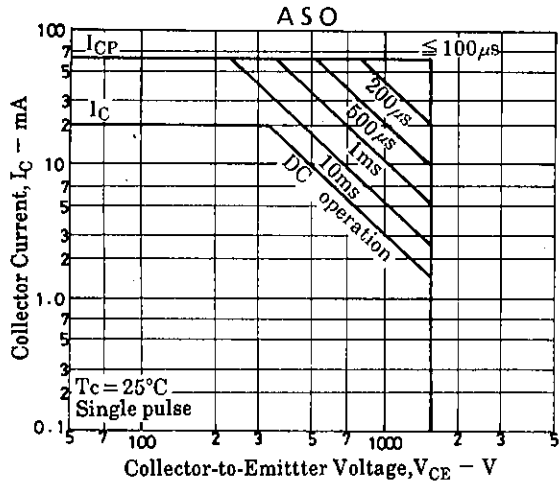


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